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**Uwe F.W. Behringer
Wilhelm Maurer**
Editors

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Contents

ix	Conference Committees
xiii	Foreword
xv	Cooperating Partners and Sponsors
xvii	Best Poster from BACUS 2011 <i>Optimization of mask shot count using MB-MDP and lithography simulation [8166-110]</i> G. S. Chua, W. L. Wang, B. I. Choi, GLOBALFOUNDRIES Singapore (Singapore); Y. Zou, C. Tabery, GLOBALFOUNDRIES Inc. (United States); I. Bork, T. Nguyen, A. Fujimura, D2S Inc. (United States)

PLENARY SESSION

8352 02	Nanometer-level semiconductor imaging for micrometer-level MEMS (Keynote Paper) [8352-100] B. J. Lin, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)
8352 03	Mask industry assessment trend analysis: 2012 (Invited Paper) [8352-36] Y. D. Chan, SEMATECH North (United States)

EUV LITHOGRAPHY AND MASK APPLICATION

8352 04	Mask readiness for EUVL pilot line (Invited Paper) [8352-28] N. Hayashi, T. Abe, T. Takikawa, Dai Nippon Printing Co., Ltd. (Japan)
8352 05	NXE:3100 full wafer imaging performance and budget verification [8352-09] E. van Setten, K. van Ingen Schenau, M. O'Mahony, T. Hollink, F. Wittebrood, N. Davydova, M. Eurlings, K. Feenstra, J. Finders, ASML Netherlands B.V. (Netherlands); M. Dusa, ASML (Belgium); S. Young, ASML Netherlands B.V. (Netherlands)
8352 07	A fast approach to model EUV mask 3D and shadowing effects [8352-23] Y. Li, D. Peng, M. Satake, P. Hu, Luminescent Technologies, Inc. (United States)
8352 08	EUVL mask performance and optimization [8352-19] N. Davydova, R. de Kruif, E. van Setten, ASML Netherlands B.V. (Netherlands); B. Connolly, Toppan Photomasks, Inc. (Germany); K. Mehagnoul, ASML Netherlands B.V. (Netherlands); J. Zimmerman, N. Harned, ASML (United States); F. Kalk, Toppan Photomasks, Inc. (United States)

MASK OPTIMIZATION

- 8352 09 **AIMS D2DB simulation for DUV and EUV mask inspection** [8352-18]
D. Peng, Y. Li, M. Satake, P. Hu, Luminescent Technologies, Inc. (United States); J. Chen, S. C. Hsu, R. Lai, C. S. Lin, L. C. C. Tuo, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)
- 8352 0A **Correcting image placement errors using registration control (RegC) technology in the photomask periphery (Best Paper of EMLC 2012)** [8352-11]
A. Cohen, Carl Zeiss SMS Ltd. (Israel); F. Lange, Advanced Mask Technology Ctr. GmbH Co. KG (Germany); G. Ben-Zvi, E. Graitzer, V. Dmitriev, Carl Zeiss SMS Ltd. (Israel)

LITHOGRAPHY OPTIMIZATION

- 8352 0B **Optimization method of photolithography process by means of atomic force microscopy** [8352-05]
A. Sierakowski, P. Janus, Institute of Electron Technology (Poland); D. Kopiec, K. Nieradka, Wrocław Univ. of Technology (Poland); K. Domanski, P. Grabiec, Institute of Electron Technology (Poland); T. Gotszalk, Wrocław Univ. of Technology (Poland)
- 8352 0C **Investigation and mitigation of field-edge CDU fingerprint for ArFi lithography for 45-nm to sub-28-nm logic nodes** [8352-10]
B. Le-Gratiet, STMicroelectronics (France); J. Finders, O. Mouraille, R. Queens, M. Escalante, B. Smeets, J. Beltman, ASML Netherlands B.V. (Netherlands); K. Jullian, STMicroelectronics (France)
- 8352 0D **Double exposure as a method to correct on-wafer CD variations: a proposal** [8352-32]
A. Hotzel, H. Bald, GLOBALFOUNDRIES Dresden Module One LLC & Co. KG (Germany)

LITHOGRAPHY FOR MEMS

- 8352 0E **Lithographic aspects for the fabrication of BiCMOS embedded bio-MEMS and RF-MEMS** [8352-04]
P. Kulse, M. Birkholz, K.-E. Ehwald, M. Kaynak, M. Wietstruck, J. Bauer, J. Drews, K. Schulz, IHP GmbH (Germany)
- 8352 0F **MEMS: fabrication of cryogenic bolometers** [8352-34]
J. Kunert, S. Anders, T. May, V. Zakosarenko, G. Zieger, Institute of Photonic Technology (Germany); E. Kreysa, Max Planck Institute for Radioastronomy (Germany); H.-G. Meyer, Institute of Photonic Technology (Germany)

MASK MATERIALS

- 8352 OG **Impact of reticle absorber on the imaging properties in ArFi lithography (Invited Paper)** [8352-03]
J. Finders, O. Mouraille, A. Bouma, A. Ngai, K. Grim, J. van Praagh, C. Toma, ASML Netherlands B.V. (Netherlands); J. Miyazaki, ASML Japan Co., Ltd. (Japan); M. Higuchi, Y. Kojima, Toppan Printing Co., Ltd. (Japan); B. Connolly, Toppan Photomasks, Inc. (Germany); I. Englard, Y. Cohen, S. Mangan, M. Ben Yishai, Applied Materials, Inc. (Israel); K. Jullian, STMicroelectronics (France)
- 8352 OH **PSM and thin OMOG reticles aerial imaging metrology comparison study** [8352-12]
Y. Cohen, Applied Materials, Inc. (Israel); J. Finders, ASML Netherlands B.V. (Netherlands); S. Mangan, Applied Materials, Inc. (Israel); I. Englard, Applied Materials B.V. (Netherlands); O. Mouraille, M. Janssen, ASML Netherlands B.V. (Netherlands); J. Miyazaki, ASML Japan Co., Ltd. (Japan); B. Connolly, Toppan Photomasks, Inc. (Germany); Y. Kojima, M. Higuchi, Toppan Printing Co., Ltd. (Japan)

MASK DATA PREPARATION

- 8352 OI **Pointwise process proximity function calibration: PPExplorer application results** [8352-17]
M. Krueger, EQUIcon Software GmbH Jena (Germany); M. Banasch, Vistec Electron Beam GmbH (Germany); R. Galler, D. Melzer, EQUIcon Software GmbH Jena (Germany); L. E. Ramos, Vistec Electron Beam GmbH (Germany); M. Suelzle, EQUIcon Software GmbH Jena (Germany); U. Weidenmueller, Vistec Electron Beam GmbH (Germany); U. Zeitner, Fraunhofer Institute for Applied Optics and Precision Engineering (Germany)
- 8352 OJ **Mask write time reduction: deployment of advanced approaches and their impact on established work models** [8352-33]
S. F. Schulze, A. Elayat, T. Lin, E. Sahouria, Mentor Graphics Corp. (United States)
- 8352 OK **Improvements on Corner2, a lossless layout image compression algorithm for maskless lithography systems** [8352-30]
J. Yang, Univ. of Michigan (United States); S. A. Savari, Texas A&M Univ. (United States)

EMERGING LITHOGRAPHY

- 8352 OM **Enhanced e-beam pattern writing for nano-optics based on character projection** [8352-15]
E.-B. Kley, H. Schmidt, Friedrich-Schiller-Univ. Jena (Germany); U. Zeitner, Fraunhofer Institute for Applied Optics and Precision Engineering (Germany); M. Banasch, B. Schnabel, Vistec Electron Beam GmbH (Germany)
- 8352 ON **A novel tool for frequency assisted thermal nanoimprint (T-NIL)** [8352-06]
A. Mayer, K. Dhima, S. Möllenbeck, S. Wang, H.-C. Scheer, Bergische Univ. Wuppertal (Germany)

8352 0O **Nanoimprint activities in Austria in the research project cluster NILaustria** [8352-21]
M. Mühlberger, H. Fachberger, I. Bergmair, M. Rohn, B. Dittert, R. Schöffner, PROFACTOR GmbH (Austria); T. Rothländer, D. Nees, U. Palfinger, A. Haase, A. Fian, JOANNEUM RESEARCH Forschungsgesellschaft mbH (Austria); M. Knapp, OnkoTec GmbH (Austria); C. Preininger, AIT Austrian Institute of Technology GmbH (Austria); G. Kreindl, M. Kast, EV Group (Austria); T. Fromherz, Johannes Kepler Univ. Linz (Austria)

8352 0P **Phase-shift at subwavelength holographic lithography (SWHL)** [8352-02]
M. V. Borisov, D. A. Chelyubeev, V. V. Chernik, A. A. Gavrikov, D. Yu. Knyazkov, P. A. Mikheev, V. I. Rakhovsky, A. A. Shamaev, Nanotech SWHL (Russian Federation)

MASK HANDLING, CLEANING, AND HAZE

8352 0Q **High quality mask storage in an advanced Logic-Fab** [8352-27]
C. Jähnert, S. Fritsche, Infineon Technologies Dresden GmbH (Germany)

8352 0R **Through pellicle management of haze formation in a wafer fabrication environment** [8352-07]
A. Figliolini, M. Archuletta, J. LeClaire, D. Brinkley, D. Doerr, R. White, R. Bozak, D. A. Lee, RAVE LLC (United States)

8352 0S **Cleaning aspects of material choice for high end mask manufacturing** [8352-16]
P. Nesladek, Advanced Mask Technology Ctr. GmbH Co. KG (Germany); S. Osborne, Osborne Enterprise (Germany); S. Rummelin, Advanced Mask Technology Ctr. GmbH Co. KG (Germany)

8352 0T **The effect of puddle megasonic cleaning for advanced photomask with subresolution assist features (SRAFs)** [8352-20]
M.-C. Chen, H.-J. Yang, C.-R. Tseng, Taiwan Mask Corp. (Taiwan)

EUV MASK DEFECT MANAGEMENT

8352 0U **Integrated cleaning and handling automation of NXE3100 reticles (Invited Paper)** [8352-31]
R. Jonckheere, IMEC (Belgium); T. Waehler, HamaTech APE GmbH & Co. KG (Germany); B. Baudemprez, IMEC (Belgium); U. Dietze, SUSS MicroTec Inc. (United States); P. Dress, O. Brux, HamaTech APE GmbH & Co. KG (Germany); K. Ronse, IMEC (Belgium)

8352 0V **Towards the optical inspection sensitivity optimization of EUV masks and EUVL-exposed wafers** [8352-29]
U. Okoroanyanwu, GLOBALFOUNDRIES Inc. (Germany); J. Heumann, Advanced Mask Technology Ctr. GmbH Co. KG (Germany); X. Zhu, C. H. Clifford, F. Jiang, P. Mangat, GLOBALFOUNDRIES Inc. (United States); R. Ghaskadvi, KLA-Tencor Corp. (United States); E. Mohn, R. Moses, Advanced Mask Technology Ctr. GmbH Co. KG (Germany); O. Wood, GLOBALFOUNDRIES Inc. (United States); H. Rolff, T. Schedel, R. Cantrell, P. Nesladek, Advanced Mask Technology Ctr. GmbH Co. KG (Germany); N. LiCausi, X. Cai, W. Taylor, J. Schefske, GLOBALFOUNDRIES Inc. (United States); M. Bender, Advanced Mask Technology Ctr. GmbH Co. KG (Germany); N. Schmidt, KLA-Tencor Germany (Germany)

8352 0W **EUV mask defects and their removal** [8352-37]
A. Rastegar, V. Jindal, SEMATECH North (United States)

- 8352 0X **EUVL defect printability: an industry challenge** [8352-26]
H. J. Kwon, R. Teki, J. Harris-Jones, A. Cordes, SEMATECH North (United States)
- 8352 0Y **Advanced metrology techniques for the characterization of EUV mask blank defects**
[8352-24]
J. Harris-Jones, V. Jindal, C. C. Lin, T. Chakraborty, E. Stinzianni, R. Teki, H. J. Kwon, SEMATECH
North (United States)

Author Index

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- 2 Plenary Session II
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N. Hayashi*, Dai Nippon Printing Company Ltd. (Japan)
- 3 EUV Lithography and Mask Application
T. Scherübl*, Carl Zeiss SMS GmbH (Germany)
B. Connolly*, Toppan Photomasks Inc. (Germany)
- 4 Mask Optimization
D. Farrar, HOYA Corporation (United Kingdom)
F. Goodwin, SEMATECH North (United States)
- 5 Lithography Optimization
J. Finders*, ASML Netherlands B.V. (Netherlands)
J. Whittey*, KLA-Tencor Corporation (United States)
- 6 Lithography for MEMS
J. Bauer*, IHP GmbH (Germany)
U. F.W. Behringer*, UBC Microelectronics (Germany)
- 7 Mask Materials
H. Wolf*, Photronics MZD GmbH (Germany)
R. Seltmann*, GLOBALFOUNDRIES, Inc. (Germany)
- 8 Mask Data Preparation
I. Stolberg*, Vistec Electron Beam GmbH Jena (Germany)
W. Maurer*, Infineon Technologies AG (Germany)

- 9 Emerging Lithography
H.-C. Scheer*, Bergische Universität Wuppertal (Germany)
S. Tedesco*, CEA-LETI (France)
- 10 Mask Handling, Cleaning, and Haze
N. Hayashi*, Dai Nippon Printing Company Ltd. (Japan)
R. Jonckheere*, IMEC (Belgium)
- 11 EUV Mask Defect Management
F. Goodwin, SEMATECH North (United States)
C. Gale*, Applied Materials (Germany)
- 12 Last Minute Submissions
U. F.W. Behringer*, UBC Microelectronics (Germany)

Foreword

Welcome to the proceedings volume from the 28th European Mask and Lithography conference, EMLC2012, which was held 17–18 January 2012 at the Hilton Hotel in Dresden, Germany. On behalf of VDE/VDI-GMM, the sponsors, and the organizing committee, we are pleased to present to you these papers presented at EMLC2012.

Every year this conference brings together scientists, researchers, engineers, and technologists from research institutes and companies from around the world to present innovations at the forefront of mask lithography and mask technology. The two-day conference is dedicated to the science, technology, engineering, and application of mask and lithography technologies and associated processes, giving an overview of the present status in mask and lithography technologies and the future strategy where mask producers and users have the opportunity of becoming acquainted with new developments and results. This year's sessions included: EUV Lithography and Masks Application, Mask Optimization, Lithography Optimization, Lithography for MEMS, Mask Materials, Mask Data Preparation, Emerging Lithography, Mask Handling, Cleaning, and Haze, and EUV Mask Defect Management. For post-deadline submissions there was the "Last Minute Session" at the end of the conference.

We are pleased to report that Martin Esser, President Silicon Saxony, Dresden, provided the opening comments. Our first keynote speaker was Dr. Burn Lin from TSMC, Taiwan. His presentation was entitled "Nanometer-level semiconductor for micrometer-level MEMS." Our second keynote speaker was Dr. Paul Chipman, Vice President, Global Strategy, Toppan Photomasks Inc., of Austin, TX, USA.

An annual fixture has been SEMATECH's Trend Analysis of their Mask industry Assessment, presented this year by David Chan from SEMATECH, Albany, New York, USA.

The Best Paper of EMLC2012 was "Correcting image placement errors by using registration control (RegC) technology in the photomask periphery," by Avi Cohen, et al, from Carl Zeiss SMS, Israel.

Parallel to the Conference Presentations, a Technical Exhibition took place on Tuesday and Wednesday where companies (mask suppliers, material suppliers, and equipment suppliers) showed off their companies and products. In order to foster the exchange between the conference attendees and the exhibitors, the exhibition area also served as the place for all coffee and lunch breaks.

We hope that you enjoyed the Technical Sessions of the EMLC2012 as well as the Technical Exhibition, but also that you allowed yourself to visit Dresden, one of the most beautiful cities in Europe!

Please mark your calendar: EMLC2013 will move from January to June. So the next conference, EMLC2013, will be 25–27 June 2013 at the same location, the Hilton Hotel in Dresden, Germany.

Uwe F.W. Behringer

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